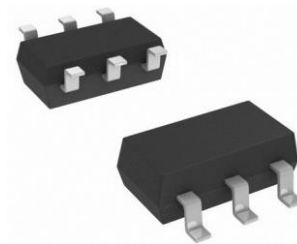
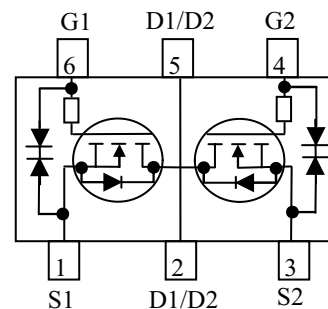
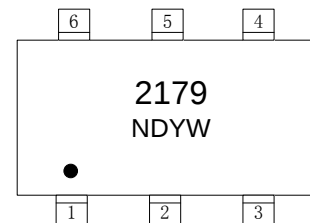


WNMD2179
Dual N-Channel, 20V, 6.3A, Power MOSFET
www.sh-willsemi.com

V_{DS} (V)	$R_{DS(on)}$ (Ω)
20	0.0175@ $V_{GS}=4.5V$
	0.0195@ $V_{GS}=3.1V$
	0.0215@ $V_{GS}=2.5V$
ESD Rating: 2000V HBM	


TSOT-23-6L

Pin configuration (Top view)


2179 = Device Code
 ND = Special Code
 Y = Year
 W = Week(A~z)

Marking
Order information

Device	Package	Shipping
WNMD2179-6/TR	TSOT-23-6L	3000/Reel&Tape

Descriptions

The WNMD2179 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WNMD2179 is Pb-free.

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package TSOT-23-6L

Applications

- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch
- Charging

Absolute Maximum ratings

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V _{GS}	±10		
Continuous Drain Current ^a	T _A =25°C	I _D	6.3	5.7	A
	T _A =70°C		5.0	4.6	
Maximum Power Dissipation ^a	T _A =25°C	P _D	1.1	0.9	W
	T _A =70°C		0.7	0.6	
Continuous Drain Current ^b	T _A =25°C	I _D	5.8	5.2	A
	T _A =70°C		4.6	4.1	
Maximum Power Dissipation ^b	T _A =25°C	P _D	0.9	0.7	W
	T _A =70°C		0.6	0.5	
Pulsed Drain Current ^c		I _{DM}	30		A
Operating Junction Temperature		T _J	150		°C
Lead Temperature		T _L	260		°C
Storage Temperature Range		T _{stg}	-55 to 150		°C

Thermal resistance ratings

Single Operation						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient Thermal Resistance ^a	t ≤ 10 s	R _{θJA}	90	108	°C/W	
	Steady State		110	130		
Junction-to-Ambient Thermal Resistance ^b	t ≤ 10 s	R _{θJA}	105	128		
	Steady State		133	158		
Junction-to-Case Thermal Resistance		Steady State	R _{θJC}	60		75
Dual Operation						
Junction-to-Ambient Thermal Resistance ^a	t ≤ 10 s	R _{θJA}	94	112	°C/W	
	Steady State		115	132		
Junction-to-Ambient Thermal Resistance ^b	t ≤ 10 s	R _{θJA}	110	132		
	Steady State		138	162		
Junction-to-Case Thermal Resistance		Steady State	R _{θJC}	63		78

a Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper

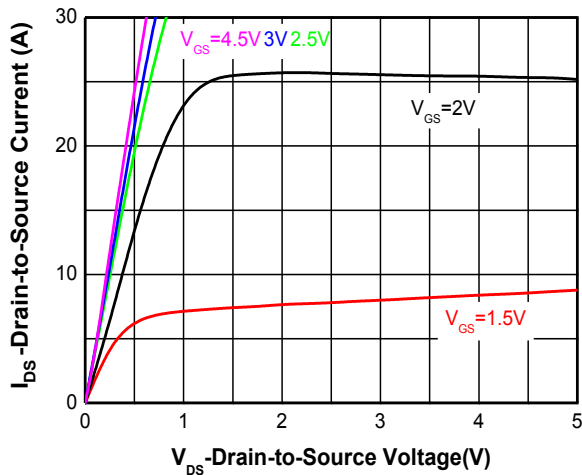
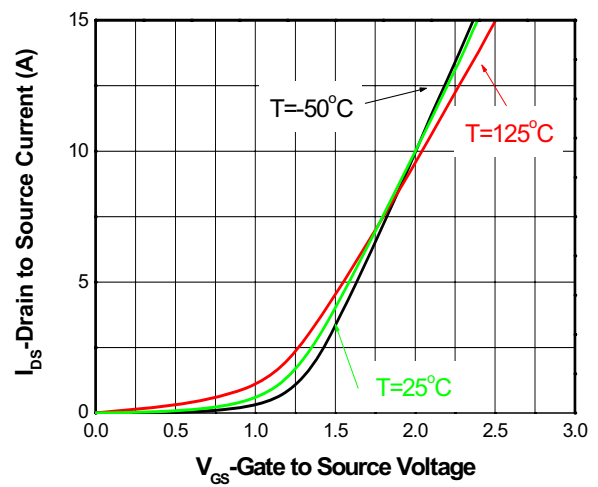
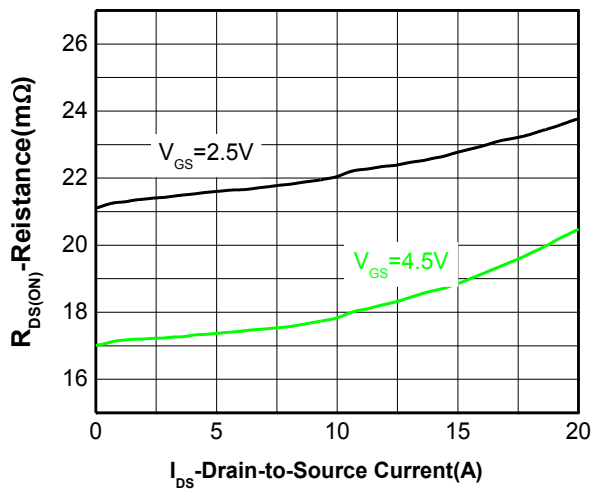
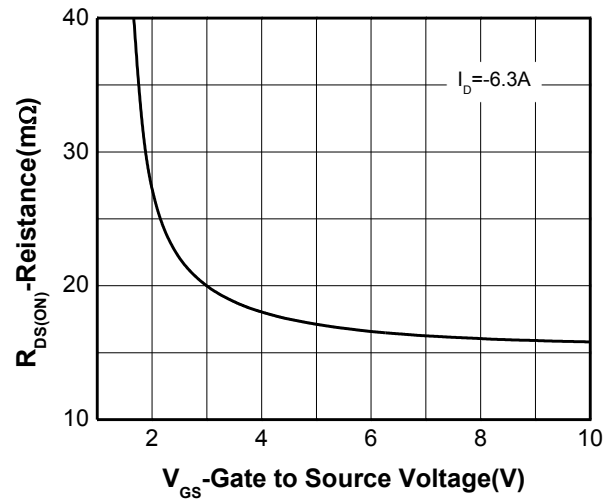
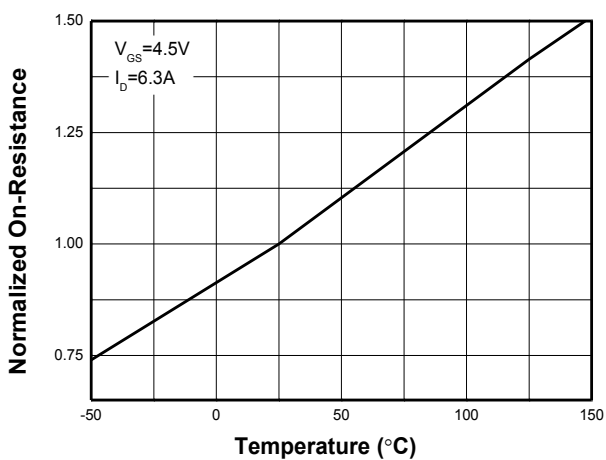
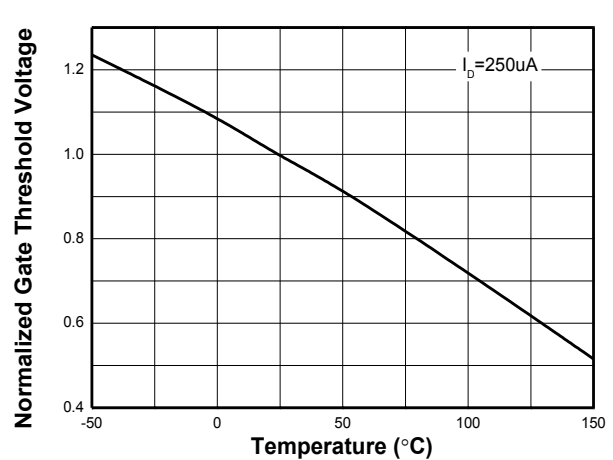
b Surface mounted on FR4 board using minimum pad size, 1oz copper

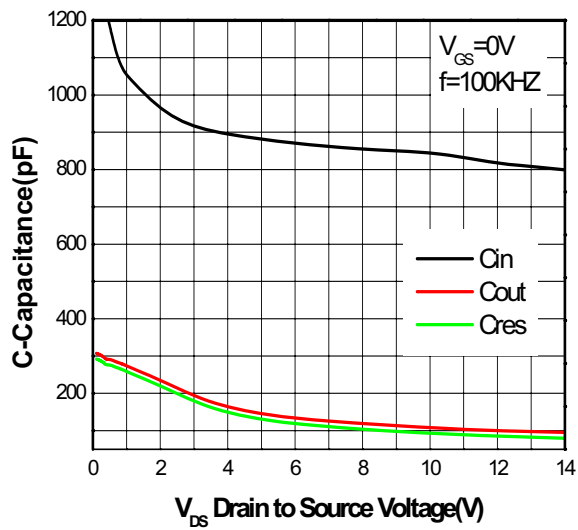
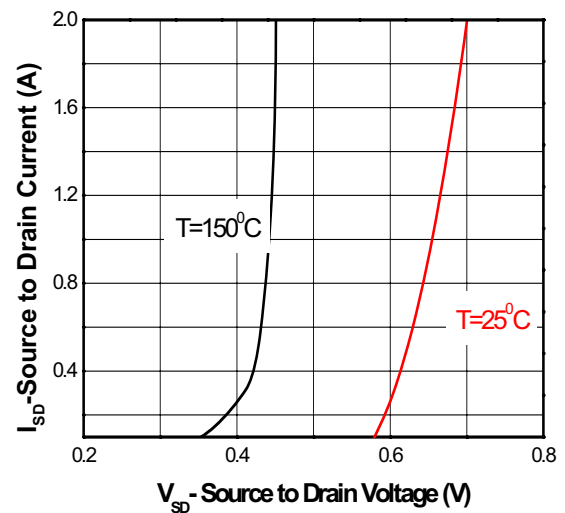
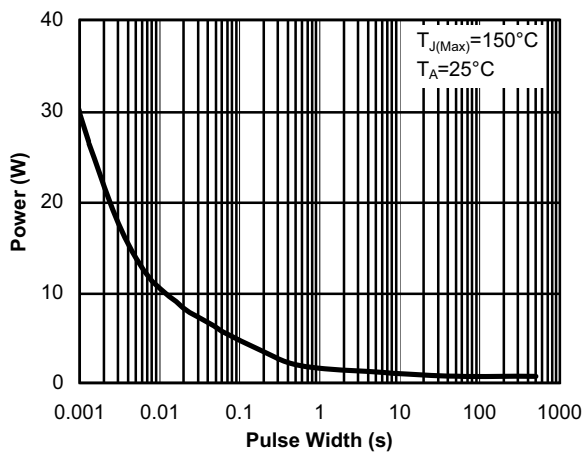
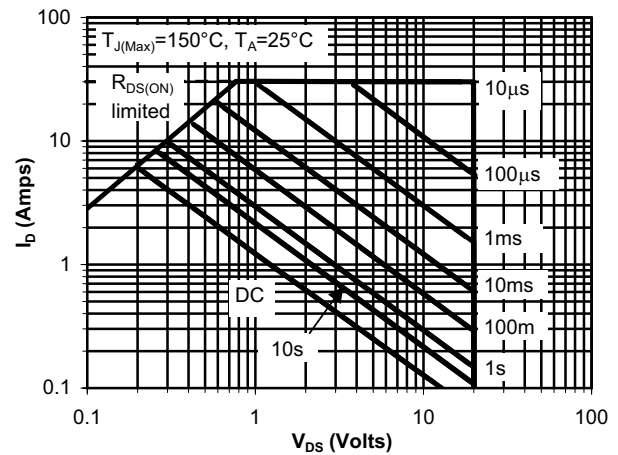
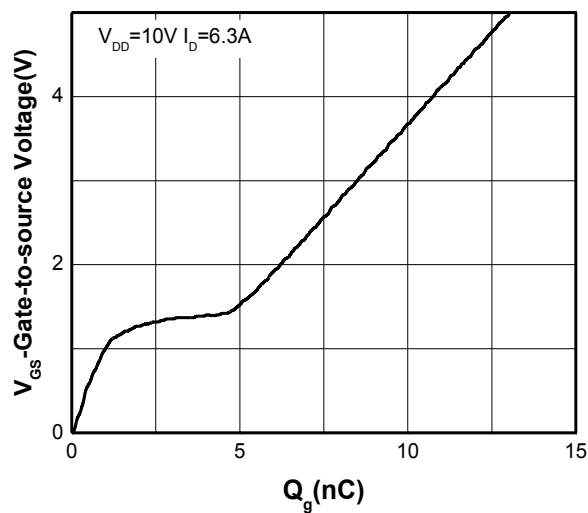
c Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

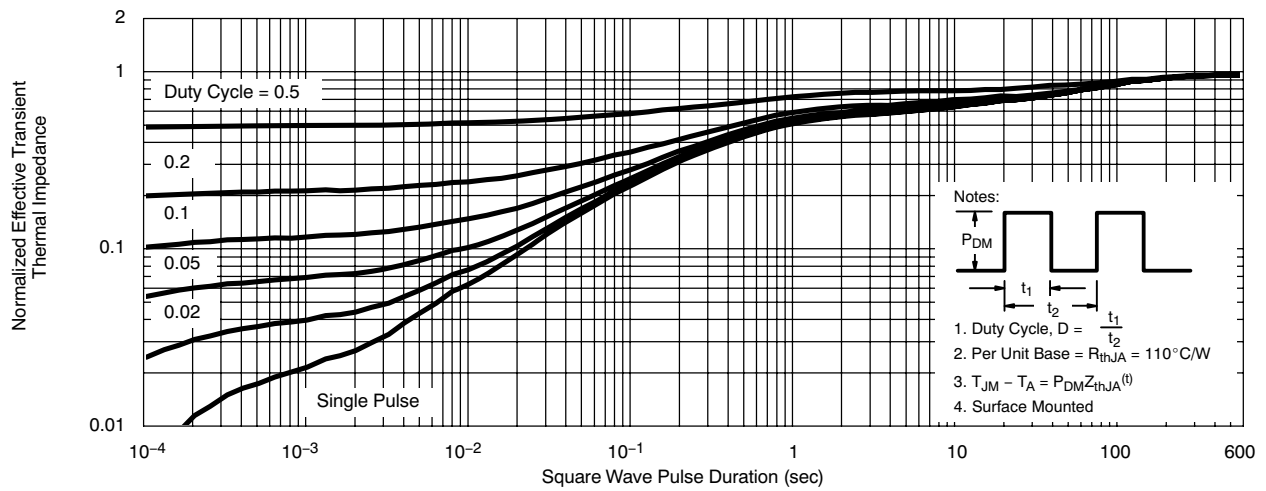
d Repetitive rating, pulse width limited by junction temperature $T_J=150^{\circ}\text{C}$.

Electronics Characteristics (Ta=25°C, unless otherwise noted)

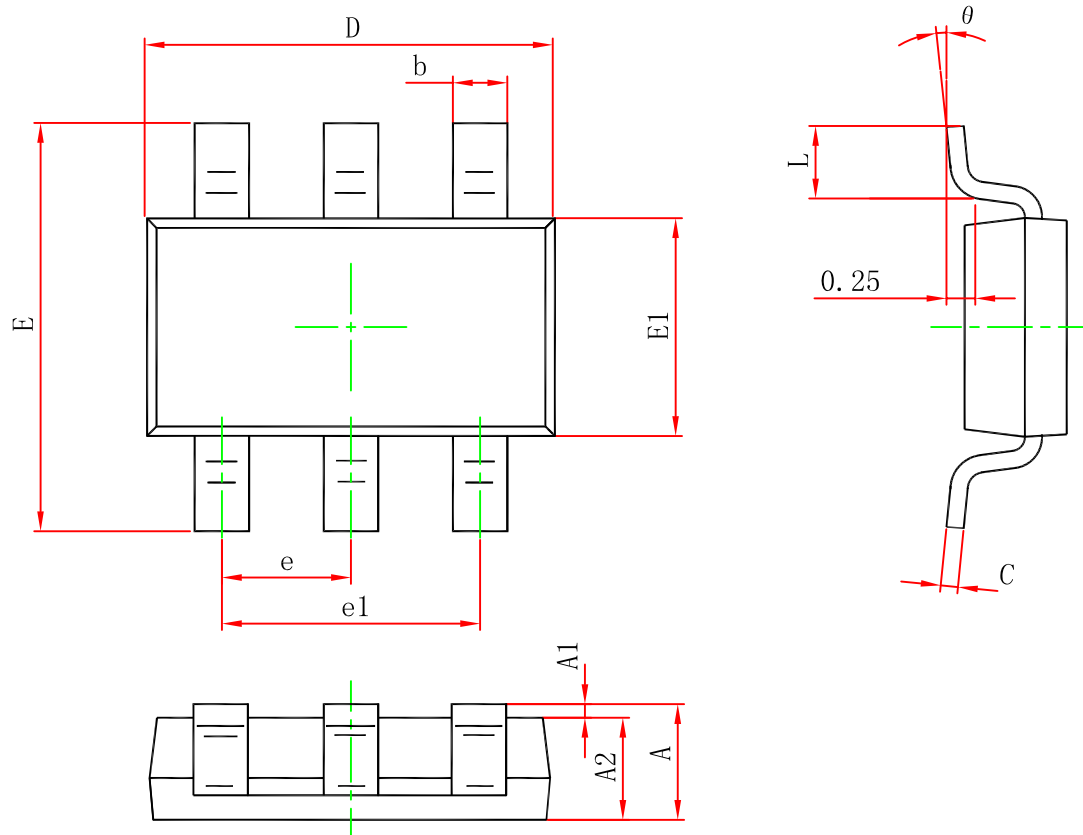
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250uA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =16 V, V _{GS} = 0V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±10V			±5	uA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250uA	0.5	0.7	1.0	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 6.3A	11	17.5	21	mΩ
		V _{GS} = 3.1V, I _D = 6.0A	13	19.5	23	
		V _{GS} = 2.5V, I _D = 5.5A	15	21.5	26	
Forward Transconductance	g _{FS}	V _{DS} = 5.0 V, I _D = 6.3A		16		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 100kHz, V _{DS} = 10 V		800		pF
Output Capacitance	C _{OSS}			108		
Reverse Transfer Capacitance	C _{RSS}			93		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 6.3 A		11.8		nC
Threshold Gate Charge	Q _{G(TH)}			0.74		
Gate-to-Source Charge	Q _{GS}			1.55		
Gate-to-Drain Charge	Q _{GD}			3.2		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V _{GS} = 4.5 V, V _{DS} =10 V, R _L =2.0 Ω, R _G =6 Ω		410		ns
Rise Time	tr			1200		
Turn-Off Delay Time	td(OFF)			6100		
Fall Time	tf			3500		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 1.0A		0.75	1.5	V

Typical Characteristics (Ta=25°C, unless otherwise noted)

Output characteristics

Transfer characteristics

On-Resistance vs. Drain current

On-Resistance vs. Gate-to-Source voltage

On-Resistance vs. Junction temperature

Threshold voltage vs. Temperature


Capacitance

Body diode forward voltage

Single pulse power

Safe operating power

Gate Charge Characteristics



Transient thermal response (Junction-to-Ambient)

Package outline dimensions
TSOT-23-6L

NOTES:

ALL DIMENSIONS MEET JEDEC STANDARD MO-193 AA
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	---	0.900	---	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b	0.350	0.500	0.014	0.020
c	0.080	0.200	0.003	0.008
D	2.820	3.020	0.111	0.119
E1	1.600	1.700	0.063	0.067
E	2.650	2.950	0.104	0.116
e	0.95 (BSC)		0.037(BSC)	
e1	1.90 (BSC)		0.075(BSC)	
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°